

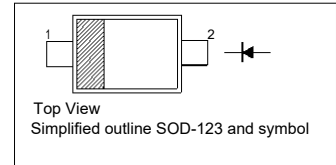
BAV101~BAV103 Silicon Epitaxial Planar Diodes

High Voltage Switching Diodes

Type	BAV101	BAV102	BAV103
MARKING	T2	T3	T4

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



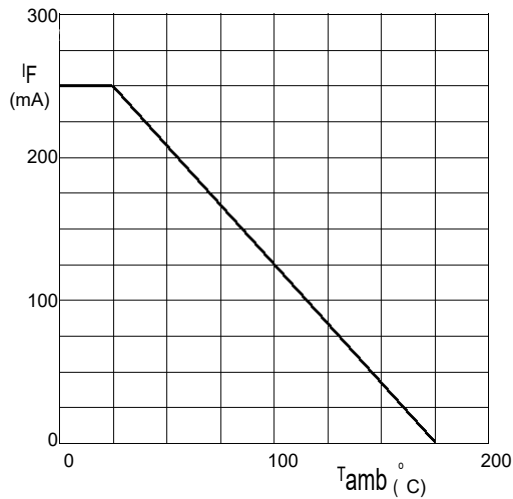
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	BAV101 120 BAV102 200 BAV103 250	V
Reverse Voltage		BAV101 100 BAV102 150 BAV103 200	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1$ s 1 at $t = 100 \mu\text{s}$ 3 at $t = 1 \mu\text{s}$ 9	A
Total Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

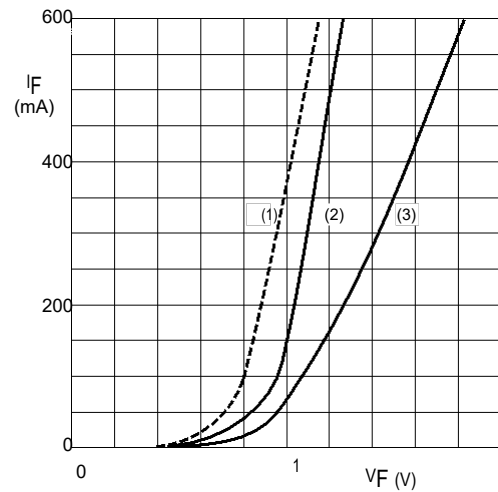
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100$ mA at $I_F = 200$ mA	V_F	1 1.25	V
Reverse Current at $V_R = 100$ V at $V_R = 150$ V at $V_R = 200$ V at $V_R = 100$ V, $T_j = 150^\circ\text{C}$ at $V_R = 150$ V, $T_j = 150^\circ\text{C}$ at $V_R = 200$ V, $T_j = 150^\circ\text{C}$		BAV101 100 BAV102 100 BAV103 100 BAV101 100 BAV102 100 BAV103 100	nA nA nA μA μA μA
Diode Capacitance at $V_R = 0$, $f = 1$ MHz	C_d	5	pF
Reverse Recovery Time at $I_F = I_R = 30$ mA, $I_{rr} = 3$ mA, $R_L = 100 \Omega$	t_{rr}	50	ns

Typical Characteristics



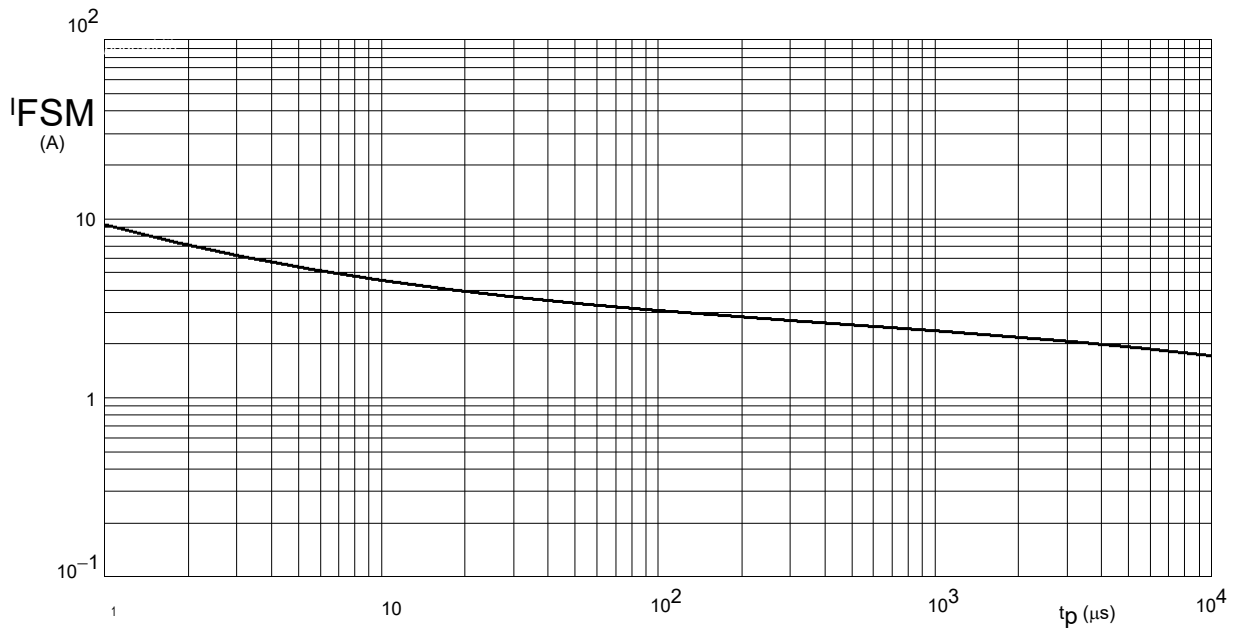
Device mounted on an FR4 printed-circuit board.

Fig.1 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 150$ °C; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

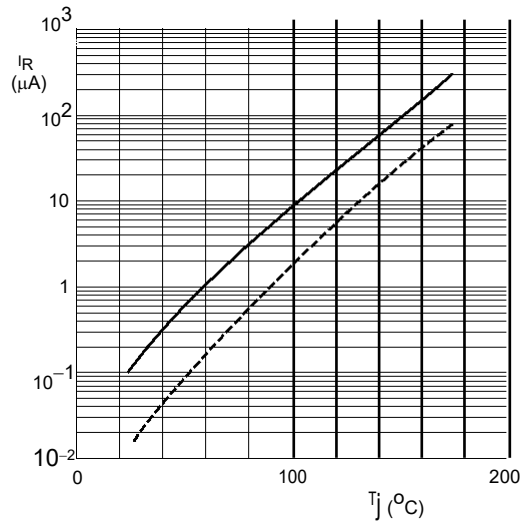
Fig.2 Forward current as a function of forward voltage.



Based on square wave currents.
 $T_j = 25$ °C prior to surge.

Fig.3 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

Typical Characteristics

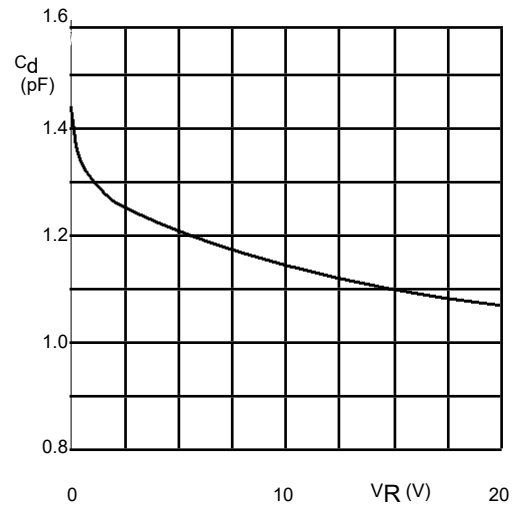


$$V_R = V_{Rmax}$$

Solid line; maximum values.

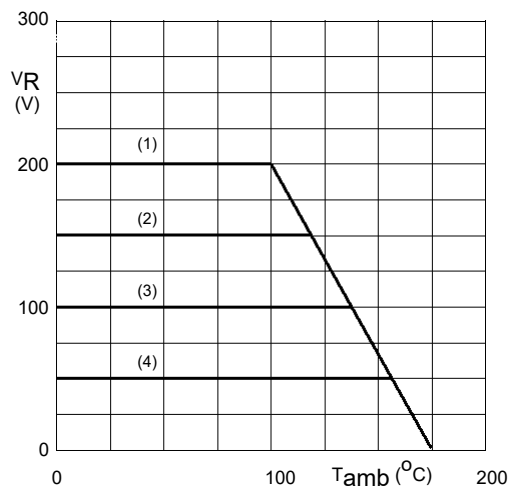
Dotted line; typical values.

Fig.4 Reverse current as a function of junction temperature.



$f = 1 \text{ MHz}$; $T_J = 25^{\circ}C$.

Fig.5 Diode capacitance as a function of reverse voltage; typical values.



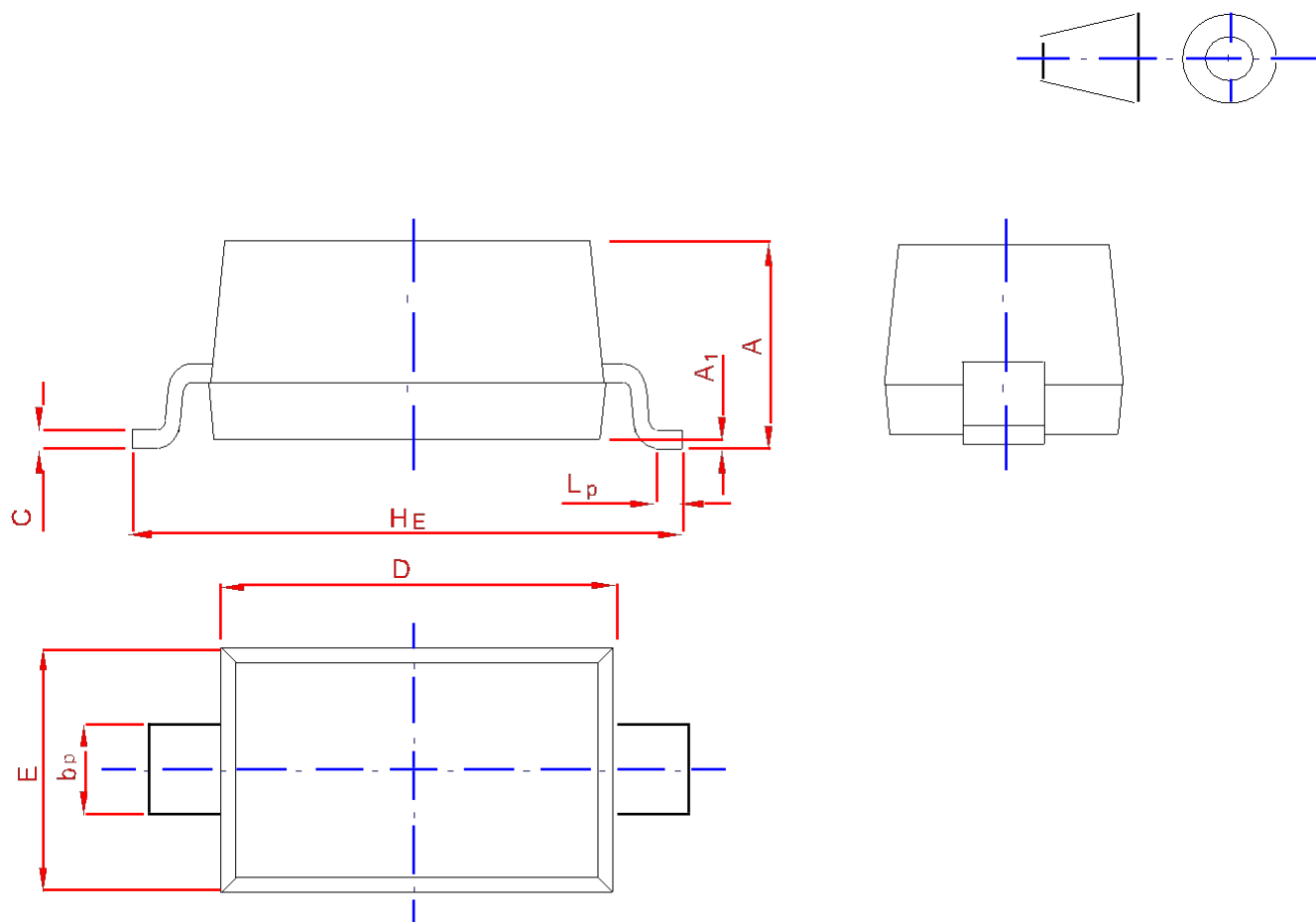
- (1) BAV103.
- (2) BAV102.
- (3) BAV101.
- (4) BAV100.

Fig.6 Maximum permissible continuous reverse voltage as a function of ambient temperature.

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	bp	C	D	E	HE	A1	Lp
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20